eo3gadt Physics of semiconductor devices Books semiconductor physics and orkghosh @ icitd.ac.in devices by D.A. Neamon B601 physics of semiconductor devices by inverter can be used to crease all S.M. SZR ond logical operations/gates K.K.Ng increase voltage - amplifier eg: op Amp decrease voltage - rectifier let the threshold current for 'on' state be lomA. even then, 9mA will be considered 'on' because there isn't sufficient difference and here difficult to sense by hordware V=IR → consequence of the ohm's Law Ohmis Law - F = FE Which leads to VEIR Resistance is different for different metals because of mobility current: no. of electrons slowing perunit density orea per length σ = restations mobility generally, a system with high or = mutal Systems with lower of = semiconductors electrons are bound with the atom due to electrostatic forces electric field goes from laner potential to down potential dx untel ut processor has thil transistors processor has - contact pins global interconnect? vias local interconnect? (nutae) transistors The vias enable us to access all billions of transistors using limited ~ 100 contact pins imp question: which material to be used TRANSISTOR Gate metal 12nm SiO2 insulator silicon substrate Semi conductor 10A = 1nm diameter of a atom: ~1-2A dimunsion of a tronsistar: ~ 200m metal gate insulator copper and Al invesion chance deplision layer suitable for via - not only cheap when electrons more between makerials, they collide These collision or inclustic no conservation of d erergy Imonutum most propable (energy here is hear energy This is the reason filament bulbs glow X: real dimension K: momentum dinersion Passing Relative 2 × Assignment 15% 4x guiz 204. Grading marksi mid sem 30% 25.1. 30% End sem 41 95% + 5% attendance ومنالهم Assignment 0 5/02 8104 deadline 18/09 15/02 calculator allowed for quizzes # Attendance 760% before & after mid sem S:/. 760% before only 2.5% 2.5% after only O1. 260%. Work